

RETRACTION

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Retraction: Enhanced resistive switching memory characteristics and mechanism using a Ti nanolayer at the W/TaO_x interface

Amit Prakash*, Siddheswar Maikap, Hsien-Chin Chiu, Ta-Chang Tien and Chao-Sung Lai

Retraction

This article is retracted.

The journal editors would like to apologise for the early publication of the original article [1], which is being retracted as it was published prior to the completion of essential revisions.

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Reference

1. Prakash A, Maikap S, Chiu HC, Tien TC, Lai CS: Enhanced resistive switching memory characteristics and mechanism using a Ti nanolayer at the W/TaO_x interface. *Nanoscale Research Letters* 2013, **8**:288.

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* Correspondence: amit.knp02@gmail.com